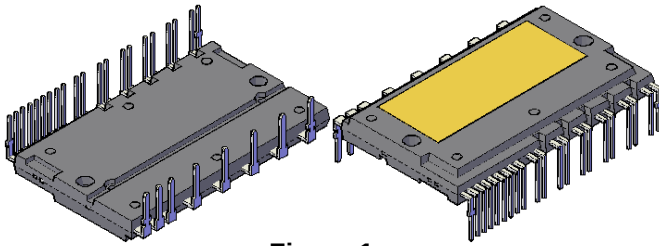


SPE20S60N-DTRANSFER-MOLD TYPE
FULL PACK TYPE**SPE20S60N-D****Figure 1****INTEGRATED POWER FUNCTIONS**

600V/20A low-loss 6th generation IGBT inverter bridge for three phase DC-to-AC power conversion.

Open emitter type.

INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS

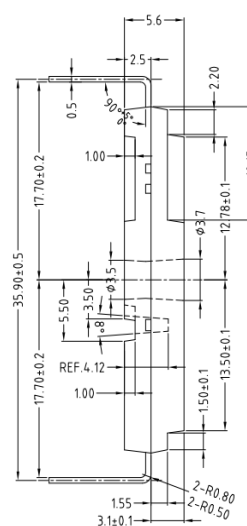
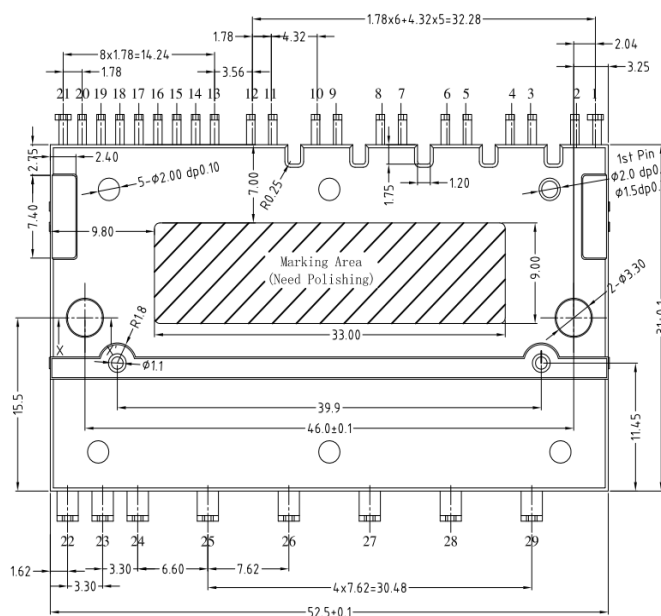
- For upper-leg IGBTs : Advanced input filter, Shoot through prevention, Drive circuit, High voltage high-speed level shifting, Control supply under-voltage (UV) protection, Short circuit protection (SC), Integrate bootstrap diodes.
- For lower-leg IGBTs : Advanced input filter, Shoot through prevention, Drive circuit, Control supply under-voltage protection (UV), Short circuit protection (SC).
- Fault signaling : Corresponding to an SC fault, a UV fault (Lower-side supply).
- Input interface: 3V, 5V line(High Active).
- Analog temperature output.

APPLICATION

AC100V~220V inverter drive for small power motor control, such as: Refrigerators、 Inverter air-conditioner、 Small Servo Motors Small Motor Control etc.

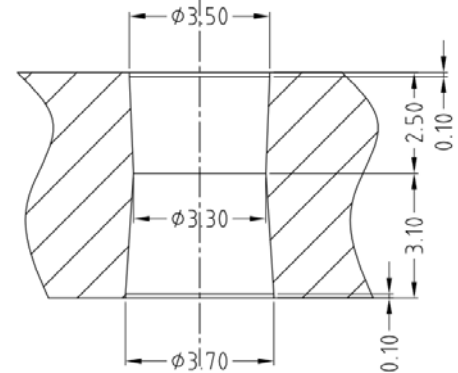
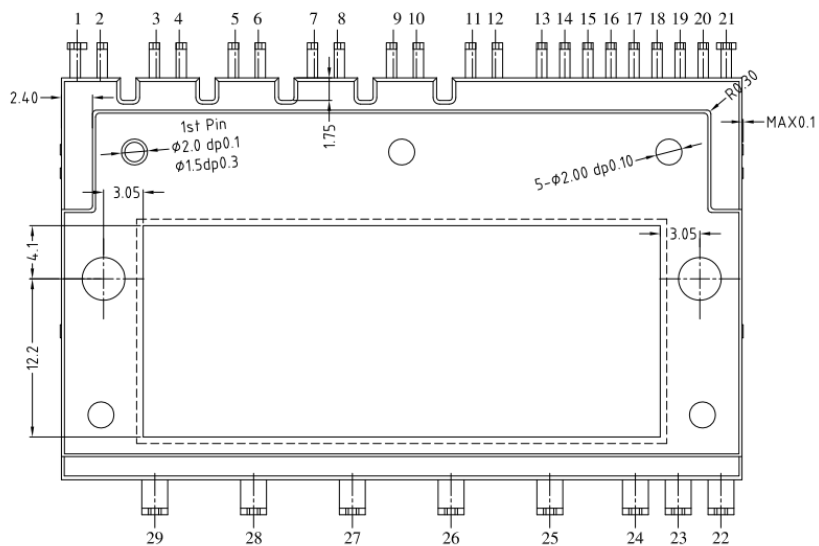
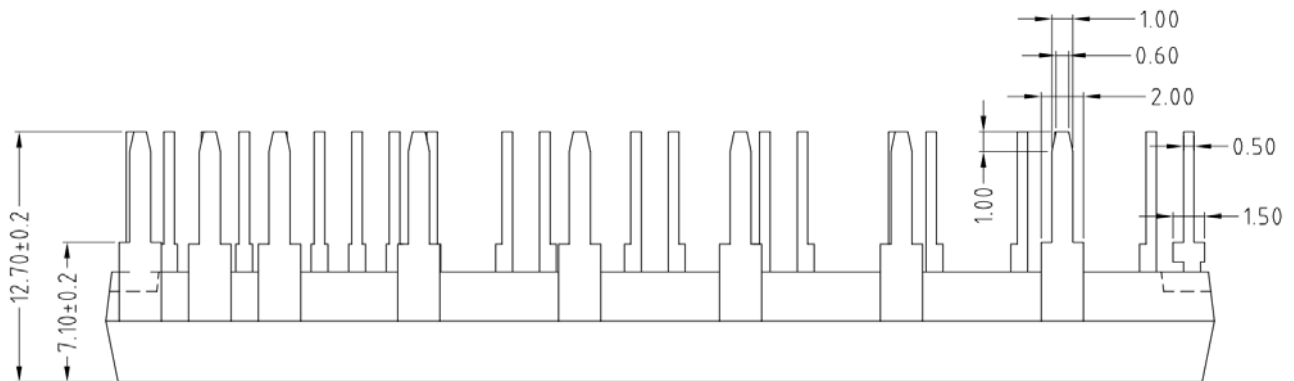
Detailed Package Outline Drawings:

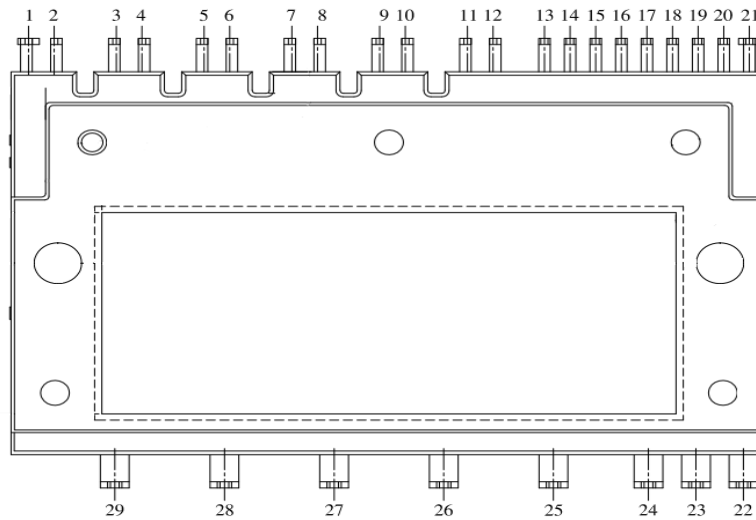
Dimensions in mm



1 VUFS	15VN
2 VUFB	16 WN
3 VP1	17 FO
4UP	18 NC
5 VVFS	19CIN
6VVFB	20 VNC
7 VP1	21 VN1
8 VP	22 NW
9 VWFS	23 NV
10 VWFB	24 NU
11 VP1	25 W
12 WP	26 V
13 VNO	27 U
14 UN	28 P
	29 NC

Dimensions in mm

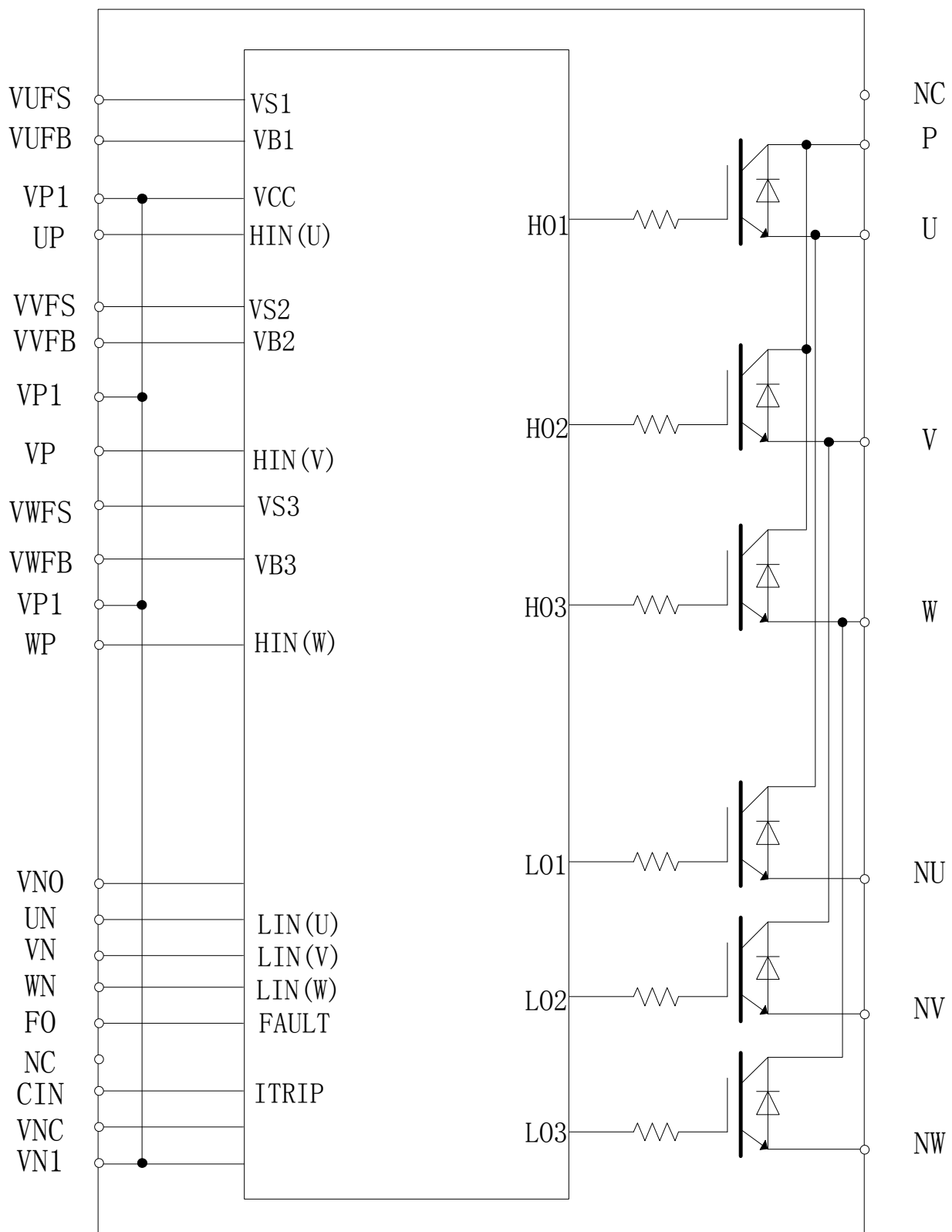


SPE20S60N-DTRANSFER-MOLD TYPE
FULL PACK TYPE**Pin Configuration****Figure 2 .Pin Configuration****Pin Descriptions**

Pin number	Pin name	Pin Description
1	VUFS	U-phase high side floating IC supply offset voltage
2	VUFB	U-phase high side floating IC supply voltage
3	VP1	IC supply voltage
4	UP	U-phase high side gate driver input
5	VVFS	V-phase high side floating IC supply offset voltage
6	VVFB	V-phase high side floating IC supply voltage
7	VP1	IC supply voltage
8	VP	V-phase high side gate driver input
9	VWFS	W-phase high side floating IC supply offset voltage
10	VWFB	W-phase high side floating IC supply voltage
11	VP1	IC supply voltage
12	WP	W-phase high side gate driver input
13	VNO	Supply Ground
14	UN	U-phase low side gate driver input
15	VN	V-phase low side gate driver input
16	WN	W-phase low side gate driver input
17	FO	Fault output
18	NC	No connection
19	CIN	Analog input for over current shutdown
20	VNC	Common Supply Ground
21	VN1	IC supply voltage
22	NW	Negative DC-Link input for W-phase
23	NV	Negative DC-Link input for V-phase
24	NU	Negative DC-Link input for U-phase
25	W	Motor W-phase output
26	V	Motor V-phase output
27	U	Motor U-phase output
28	P	Positive bus input voltage

SPE20S60N-DTRANSFER-MOLD TYPE
FULL PACK TYPE

29	NC	No connection
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Internal Function Block Diagram**Figure 3 . Function Block Diagram**

SPE20S60N-DTRANSFER-MOLD TYPE
FULL PACK TYPE**Absolute Maximum Ratings** ($T_j = 25^\circ\text{C}$, Unless Otherwise Specified)**Inverter Part**

Symbol	Parameter	Conditions	Ratings	Unit
V_{CC}	Supply Voltage	Applied between P- NU, NV, NW	450	V
$V_{CC}(\text{Surge})$	Supply Voltage (Surge)	Applied between P- NU, NV, NW	500	V
V_{CES}	Collector-emitter Voltage		600	V
$\pm I_C$	Each IGBT Collector Current	$T_C = 25^\circ\text{C}$	20	A
$\pm I_{CP}$	Each IGBT Collector Current (Peak)	$T_C = 25^\circ\text{C}$, Less than 1ms	40	A
P_C	Collector Dissipation	$T_C = 25^\circ\text{C}$ Per One Chip	78	W
T_j	Operating Junction Temperature	(Note 1)	-40 ~ +150	$^\circ\text{C}$

Note:

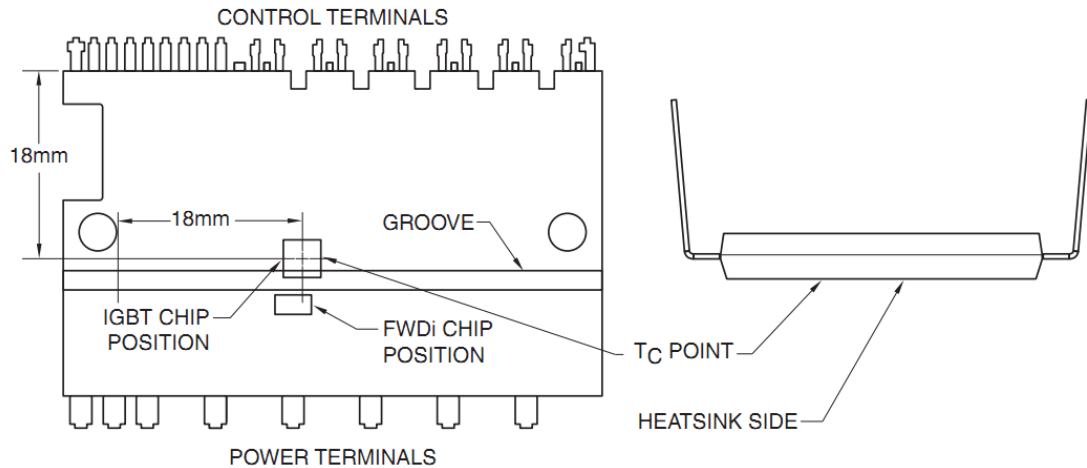
- The maximum junction temperature rating of the power chips integrated within the IPM is 175°C ($@T_C \leq 100^\circ\text{C}$). However, to insure safe operation of the IPM, the junction temperature should be limited to $T_{j(av)} \leq 150^\circ\text{C}$ ($@T_C \leq 100^\circ\text{C}$).

Control Part

Symbol	Parameter	Conditions	Ratings	Unit
V_{DB}	High side floating supply voltage	(Applied between VUFB-UUFS, VVFB-VVFS, VWFB-WWFS)	17.5	V
V_D	Low side supply voltage	Applied between VP1-VNC, VN1-VNC	17.5	V
V_{IN}	Input Signal Voltage	Applied between UP, VP, WP, UN, VN, WN - V_{NC}	-1~10	V
V_{FO}	Fault Output Supply Voltage	Applied between FO-VNC	-0.3~ $V_D+0.3$	V
I_{FO}	Fault Output Current	Sink Current at Fo Pin	1.5	mA
V_{SC}	Current Sensing Input Voltage	Applied between CIN - V_{NC}	-1~ 10	V

Total System

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CC}(\text{PROT})$	Self Protection Supply Voltage Limit(Short Circuit Protection Capability)	$V_D = V_{DB} = 13.5 \sim 16.5\text{V}$ $T_j = 150^\circ\text{C}$, Non-repetitive, less than 2us	400	V
T_C	Module Case Operation Temperature	$-20^\circ\text{C} \leq T_j \leq 150^\circ\text{C}$,	-20 ~ +100	$^\circ\text{C}$
T_{STG}	Storage Temperature		-40 ~ +150	$^\circ\text{C}$
V_{ISO}	Isolation Voltage	60Hz, Sinusoidal, AC 1 minute, between Pins and heat-sink plate	2500	V_{rms}

SPE20S60N-DTRANSFER-MOLD TYPE
FULL PACK TYPE**Figure 4. T_c measurement point****Thermal Resistance**

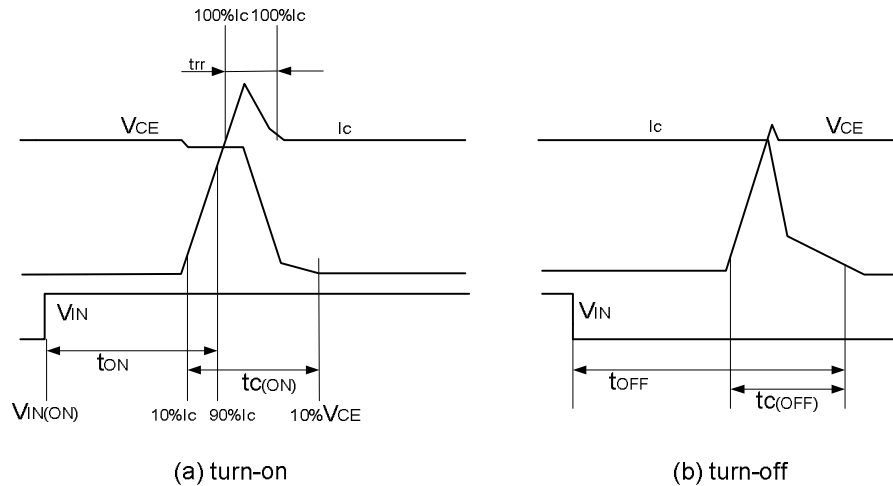
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R _{th(j-c)Q}	Junction to Case Thermal Resistance	Inverter IGBT part (per 1/6 module)	-	-	1.6	°C/W
R _{th(j-c)F}		Inverter FWD part (per 1/6 module)	-	-	2.8	°C/W

Electrical Characteristics (T_j = 25°C, Unless Otherwise Specified)**Inverter Part**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{CE(SAT)}	Collector - Emitter Saturation Voltage	V _D = V _{DB} = 15V V _{IN} = 5V, I _C = 20A, T _j = 25°C	-	1.65	-	V
		V _D = V _{DB} = 15V V _{IN} = 5V, I _C = 20A, T _j = 125°C	-	2.05	-	V
V _F	FWD Forward Voltage	V _{IN} = 0V, I _C = -20A, T _j = 25°C	-	1.5	-	V
		V _{IN} = 0V, I _C = -20A, T _j = 125°C	-	1.4	-	V
t _{ON}	Switching Times	V _{PN} = 300V, V _D = V _{DB} = 15V I _C = 20A V _{IN} = 0V ~5V, Inductive Load	-	0.78	-	μs
t _{C(ON)}			-	0.3	-	μs
t _{OFF}			-	0.8	-	μs
t _{C(OFF)}			-	0.08	-	μs
t _{rr}			-	0.2	-	μs
I _{CES}	Collector-Emitter Leakage Current	V _{CE} = V _{CES} T _j = 25°C	-	-	75	μA
		V _{CE} = V _{CES} T _j = 125°C	-	-	1	mA

Note:

2. t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. t_{C(ON)} and t_{C(OFF)} are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 5.

SPE20S60N-DTRANSFER-MOLD TYPE
FULL PACK TYPE**Figure 5 . Switching Time Definition****Electrical Characteristics** ($T_j = 25^\circ\text{C}$, Unless Otherwise Specified)**Control Part**

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
ID	Quiescent VD Supply Current	VD = 15V VIN = 5V	VP1, VN1-VNC	-	0.52	1	mA
IDB	Quiescent VDB Supply Current	VDB = 15V VIN = 5V	VUFB - U, VVFB - V, VWFB - W	-	0.36	0.55	μA
VFOH	Fault Output Voltage	Vsc = 0V, Fo Terminal pull up to 5V by 10kohm		4.9	-	-	V
VFOL		Vsc = 1V, IF0=1.0mA		-	-	1.05	V
Vsc,TH+	Short circuit positive going threshold	VD = 15V (Note 3)		0.37	0.46	0.55	V
Vsc,TH-	Short circuit negative going threshold	VD = 15V		-	0.4	-	V
UVDt	Control supply under-voltage protection	Trip Level		9.5	10.4	11.0	V
UVDr		Reset Level		11	12.1	12.8	
UVDBt		Trip Level		9.5	10.4	11.0	
UVDBr		Reset Level		11	12.1	12.8	
Ron,FLT	FLT low on resistance	I=1.5mA			50	90	ohm
tFO	Fault-out Pulse Width	CFO = 22nF		20	-	-	μs
tFIL,IN	Input filter time (U/VWP, U/VWN, CIN)	VIN = 0 V & 5 V		140	290	-	ns
tBL	CIN blanking time	VIN = 0 V or 5 V, VCIN = 5 V		-	400	-	ns
VIN(ON)	ON Threshold Voltage	Applied between UP,VP,WP,UN,VN,WN- VNC		1.7	2.1	2.4	V
VIN(OFF)	OFF Threshold Voltage			0.7	0.85	1.1	
BSD Forward voltage	VF	IF=10mA including voltage		-	1.0	1.3	V
BSD current limiting resistor	R			22	36	50	ohm

Note: 3. Short-circuit current protection is functioning at both low-side and high side.

SPE20S60N-DTRANSFER-MOLD TYPE
FULL PACK TYPE**Recommended Operating Conditions**

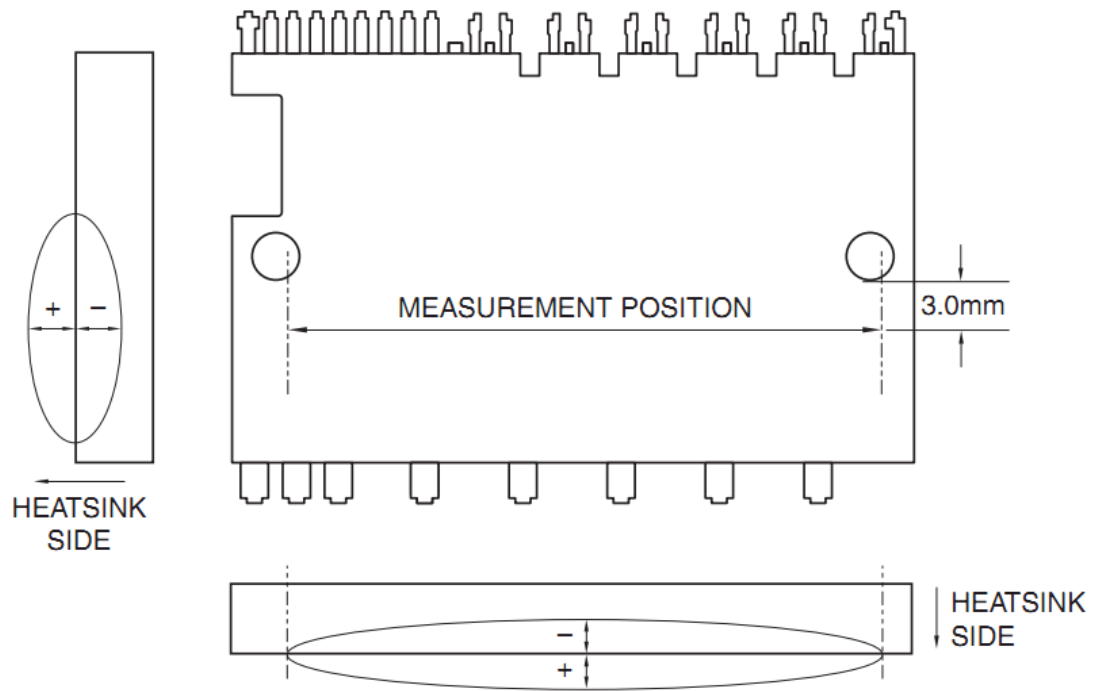
Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
V _{CC}	Supply Voltage	Applied between P - NU, NV, NW	-	300	400	V
V _D	Control Supply Voltage	Applied between VP1, VN1 - VNC	13.5	15	16.5	V
V _{DB}	High-side Bias Voltage	Applied between VUFB-VUFS, VVFB-VVFS, VWFB-VWFS	13	15	18.5	V
t _{dead}	Blanking Time for Preventing Arm-short	For Each Input Signal	1.5	-	-	us
f _{PWM}	PWM Input Signal	-20°C ≤ T _C ≤ +100°C, -20°C ≤ T _J ≤ +150°C	-	-	20	kHz
P _{WIN(ON)}	Minimum Input Pulse Width		1	-	-	us
P _{WIN(OFF)}			1	-	-	us
T _J	Junction temperature		-20	-	125	°C

Internal NTC - Thermistor Characteristics

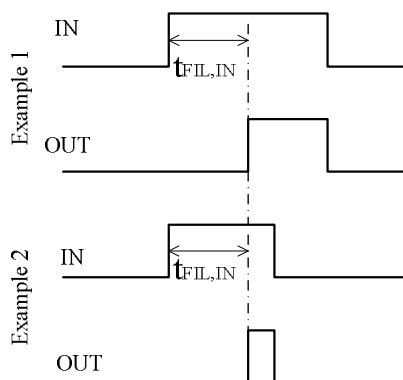
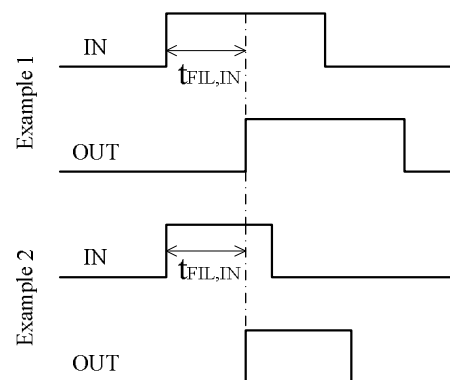
symbol	parameter	conditions	Values			unit
			Min	Typ	Max	
RNTC	Resistance of Thermistor	TNTC = 25°C see Figure 15.	98	100	102	Kohm
		TNTC = 125°C	3.43	3.58	3.75	Kohm
Temperature Range			-40	-	+125	°C

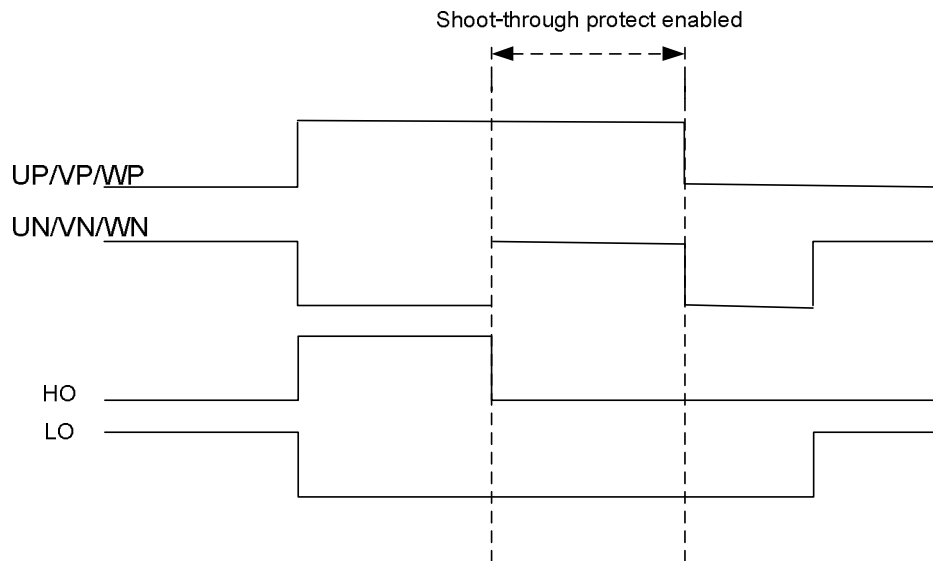
Mechanical Characteristics and Ratings

Parameter	Conditions	Limits			Unit
		Min.	Typ.	Max.	
Mounting Torque	Mounting Screw: - M3	-	0.69	-	N•m
Device Flatness	see Figure 6.	0	-	+120	um
Weight		-	7	-	g

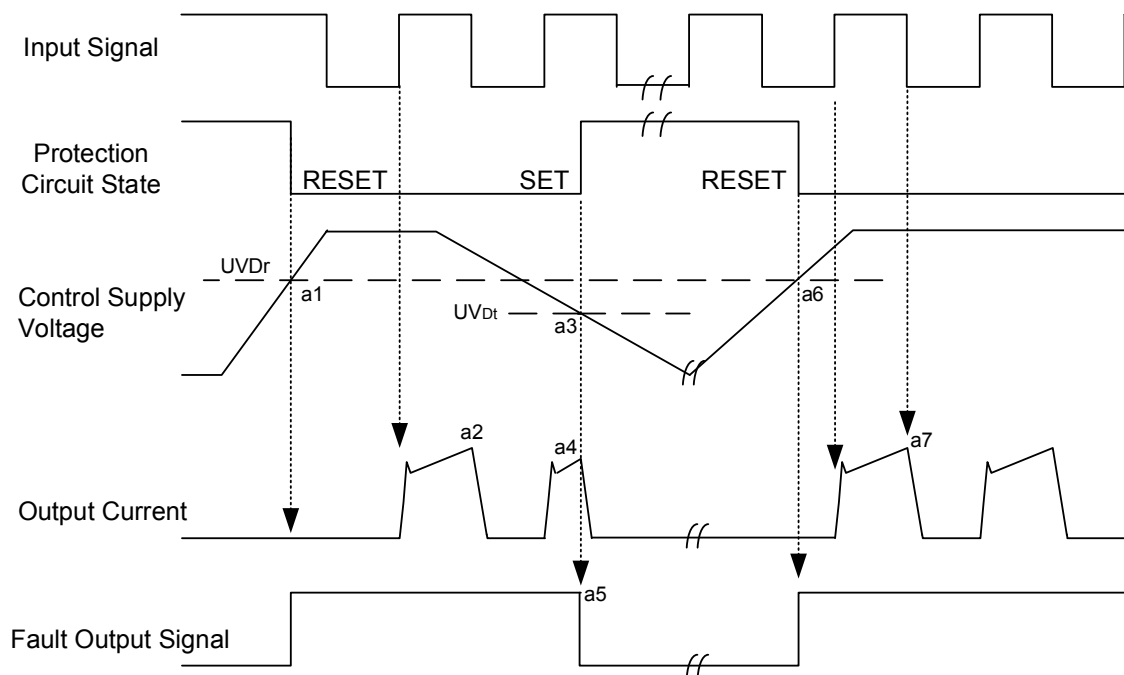
**Figure 6. Flatness Measurement Position****Advanced input filter**

The advanced input filter allows an improvement in the input/output pulse symmetry of HVIC inside the module and helps to reject noise spikes and short pulses. The advantage of the new filter is shown in Figures 7 and 8.

**Figure 7. Typical input filter****Figure 8. Advanced input filter**

Time Charts of Protective Function**Note:**

5. The signal HO and LO are gate output of the internal HVIC.

Figure 9 . Shoot-through (cross-conduction) protection

a1 : Control supply voltage rises: After the voltage rises UV_{Dr} , the circuits start to operate when next input is applied.

a2 : Normal operation: IGBT ON and carrying current.

a3 : Under voltage detection (UV_{Dt}).

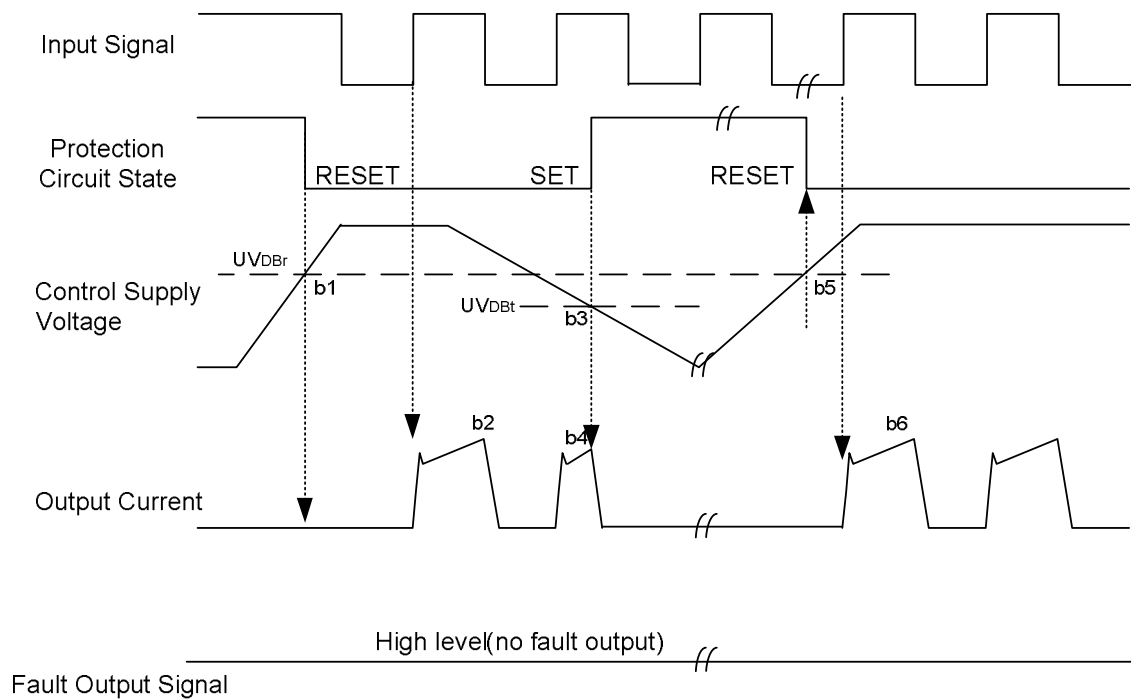
a4 : IGBT OFF in spite of control input condition.

a5 : Fault output operation starts.

a6 : Under voltage reset (UV_{Dr}).

a7 : Normal operation: IGBT ON and carrying current.

Figure 10. Under-Voltage Protection (Low-side Operation)

SPE20S60N-DTRANSFER-MOLD TYPE
FULL PACK TYPE

b1 : Control supply voltage rises: After the voltage reaches UVDBr, the circuits start to operate when next input is applied.

b2 : Normal operation: IGBT ON and carrying current.

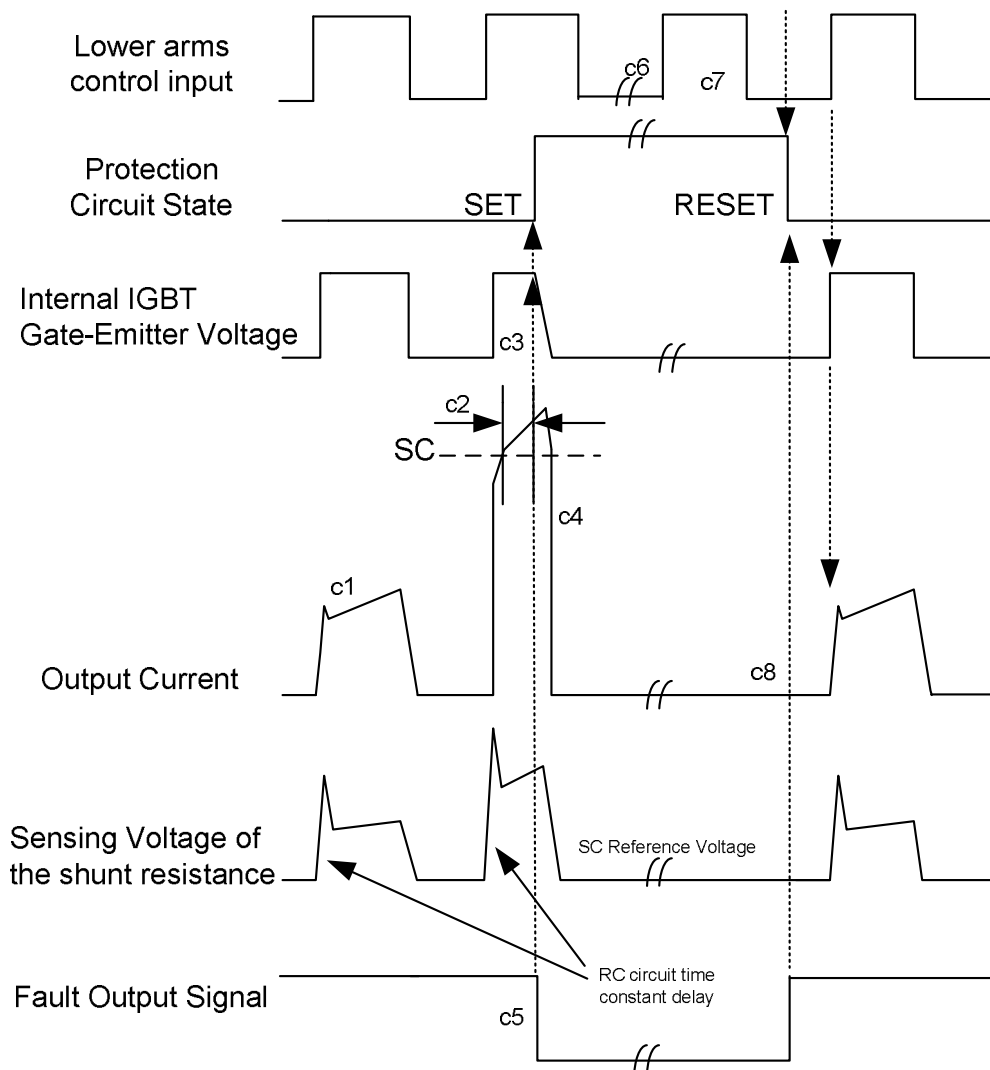
b3 : Under voltage detection (UVDBt).

b4 : IGBT OFF in spite of control input condition, but there is no fault output signal.

b5 : Under voltage reset (UVDBr).

b6 : Normal operation: IGBT ON and carrying current.

Figure 11. Under-Voltage Protection (High-side Operation only)

SPE20S60N-DTRANSFER-MOLD TYPE
FULL PACK TYPE

(with the external shunt resistance connection)

c1 : Normal operation: IGBT ON and carrying current.

c2 : Short circuit current detection (CIN trigger).

c3 : Hard IGBT gate interrupt.

c4 : IGBT turns OFF.

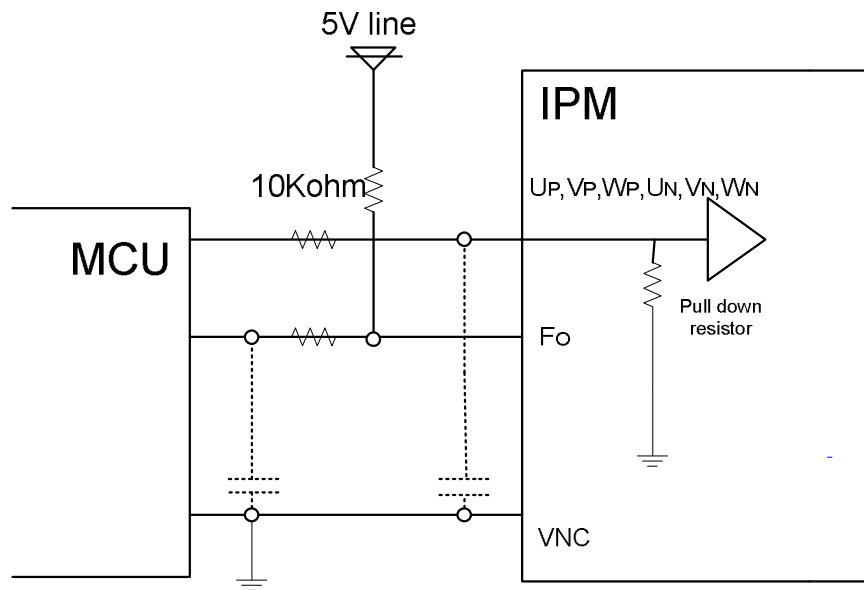
c5 : Fault output timer operation starts: The pulse width of the fault output signal is set by the internal capacitor.

c6 : Input "L" : IGBT OFF state.

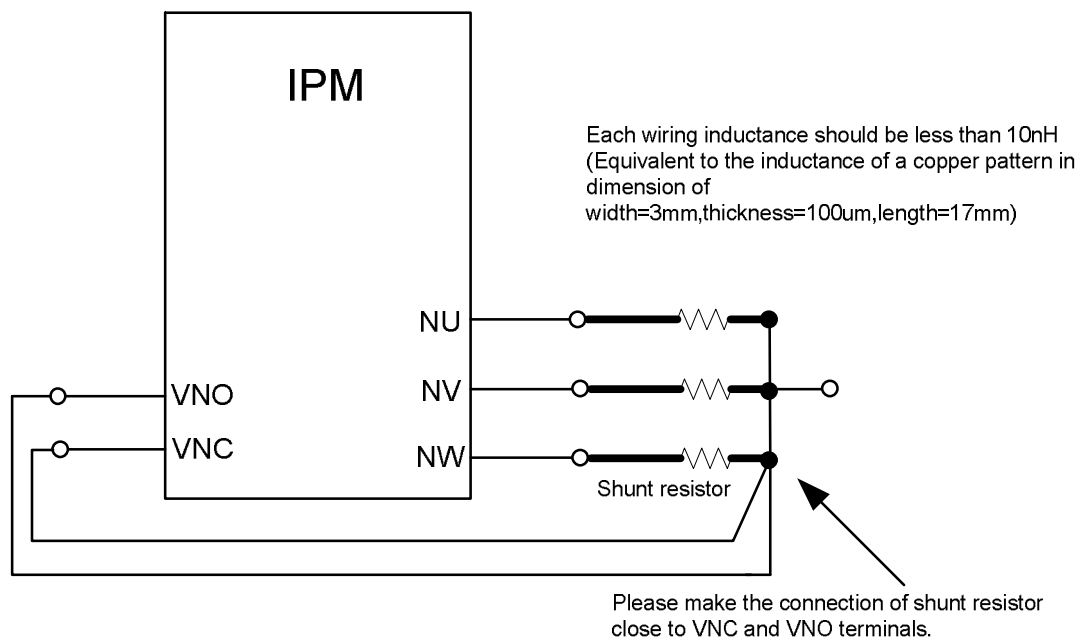
c7 : Input "H": IGBT ON state, but during the active period of fault output the IGBT doesn't turn ON.

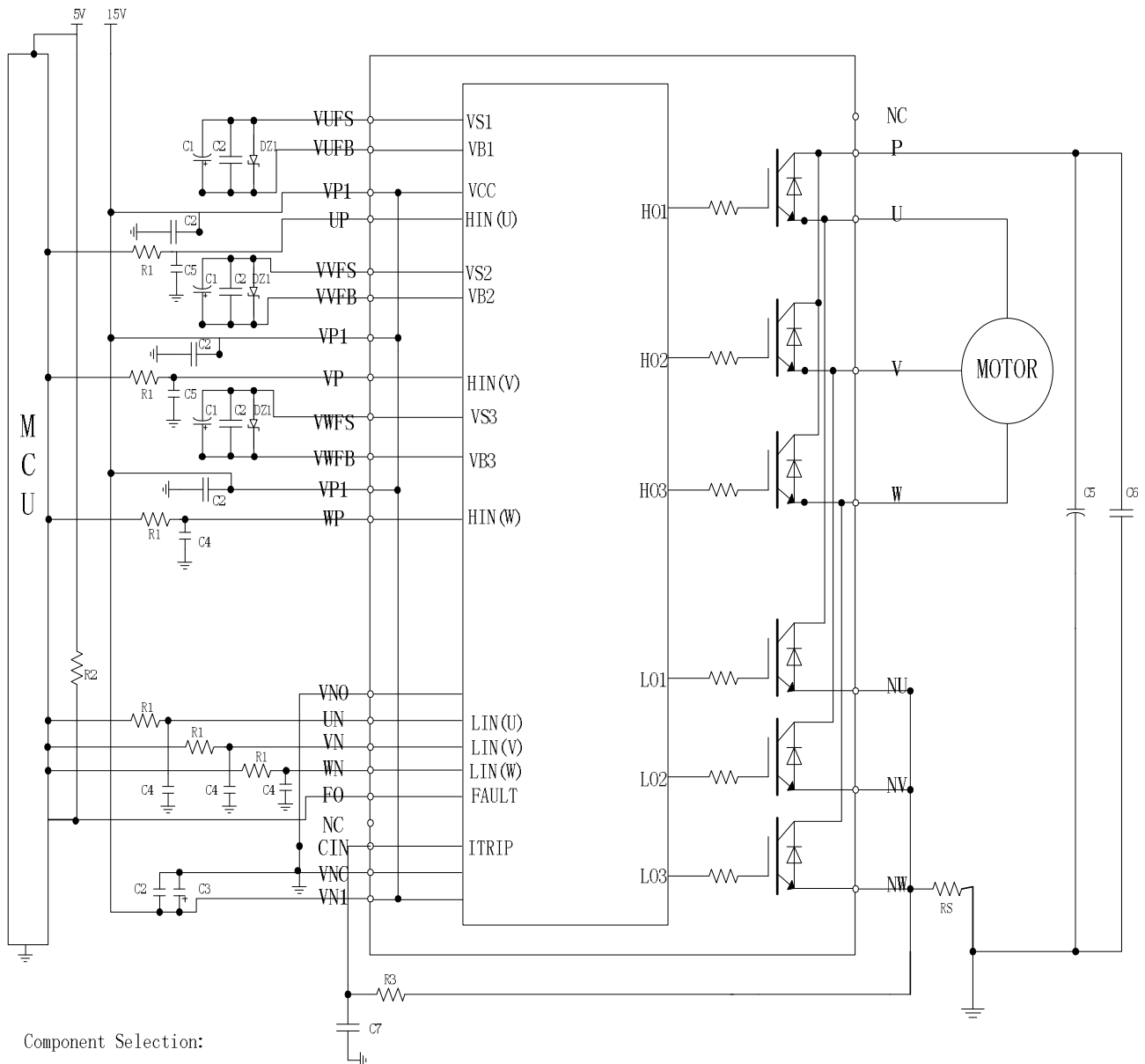
c8 : IGBT OFF state

Figure 12. Short-Circuit Current Protection (Low-side And High-side Operation)

Input/Output Interface Circuit**Figure 13. Recommended CPU I/O Interface Circuit****Note:**

6. RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board.
7. The logic input is compatible with standard CMOS or LSTTL outputs

Wiring Around The Shunt Resistor**Figure 14. Recommended Wiring Around The Shunt Resistor**

SPE20S60N-D**TRANSFER-MOLD TYPE
FULL PACK TYPE****Figure 15. Typical Application Circuit**

SPE20S60N-DTRANSFER-MOLD TYPE
FULL PACK TYPE**Note:**

- 1) Input drive is active-high type. There is a 2.5k7(min.) pull-down resistor integrated in the IC input circuit. To prevent malfunction, the wiring of each input should be as short as possible. When using RC coupling circuit, make sure the input signal level meets the turn-on and turn-off threshold voltage. See application notes for details.
- 2) Internal HVIC provides high voltage level shifting allowing direct connection of all six driving signals to the controller.
- 3) FO output is an open collector type. Pull up resistor (R3) should be adjusted to current sink capability of the controller.
- 4) To prevent input signal oscillations, minimize wire length to controller (~2cm). Additional RC filtering (C5 etc.) may be required. If filtering is added be careful to maintain proper dead time and voltage levels. See application notes for details.
- 5) All capacitors should be mounted as close to the terminals as possible. (C1: good temperature, frequency characteristic electrolytic type, and C2, C3: good temperature, frequency and DC bias characteristic ceramic type are recommended.)
- 6) Shows short circuit protection disabled. See application notes for use of short circuit protection.
- 7) Local decoupling frequency filter capacitors must be connected as close as possible to the module's pins.
- 8) The length of the DC link wiring between C4, C5, the DIP's P terminal and the shunt must be minimized to prevent excessive transient voltages. In particular C6 should be mounted as close to the DIP as possible.
- 9) Use high quality, tight tolerance current sensing resistor. Connect resistor as close as possible to the DIP's N terminal. Be careful to check for proper power rating. See application notes for calculation of resistance value.
- 10) Inserting a Zener diode (24V/1W) between each pair of control supply terminals to prevent surge destruction is recommended.